

VRW0;< ММ Ё SQS æ Ė ç s ll 1 Silicon PNP transistor in a SOT-89 Plastic Package.

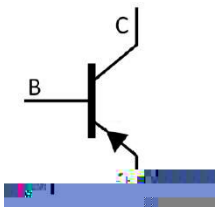
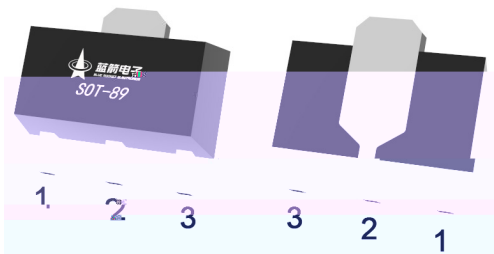
˘ М Э я > i ð º i ó ß i т ¢ я U H i ъ EU5VG4;<; T Ы ´ i ı T DHF0T434 ‰ º ˆ ˆ i ó l ð i ħ f ß

High breakdown voltage, good h_{FE} linearity, low $V_{CE(sat)}$, complements the BR2SD1898Q, Qualified to AEC-Q101 Standards for High Reliability, HF Product.

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General power amplifier applications, Meet the stringent requirements of automotive applications.

/ Equivalent Circuit



PIN1 χ Base

PIN 2 χ Collector

PIN 3 χ Emitter



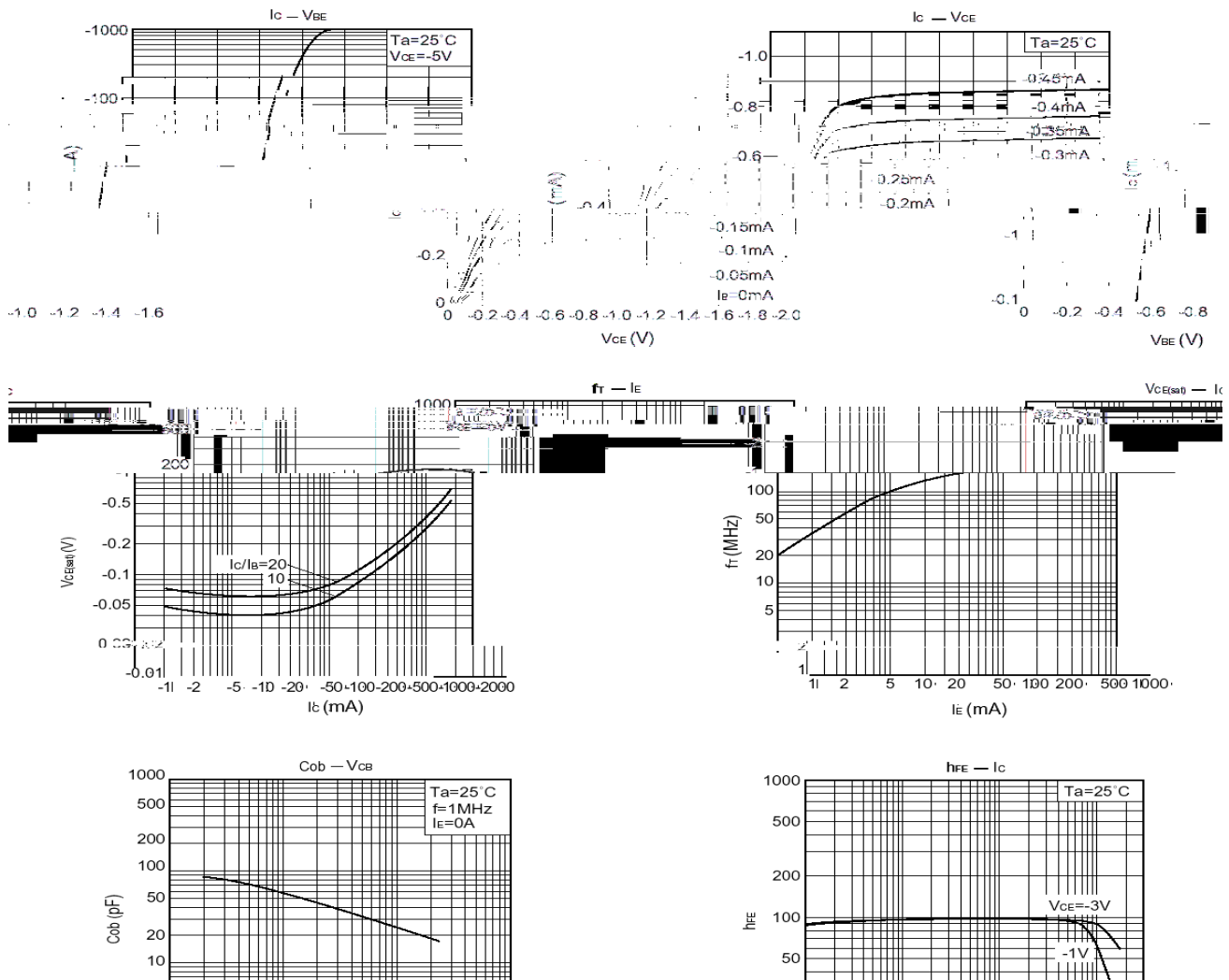
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-80	V
Collector to Emitter Voltage	V_{CEO}	-80	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current-Continuous	I_C	-1.0	A
Collector Current-Continuous(Pulse)	$*I_{CP}$	-2.0	A
Collector Power Dissipation	$**P_C$	0.5	W
	$*P_C$	2.0	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

*Single pulse $P_w=100ms$ $\leq 100ms$

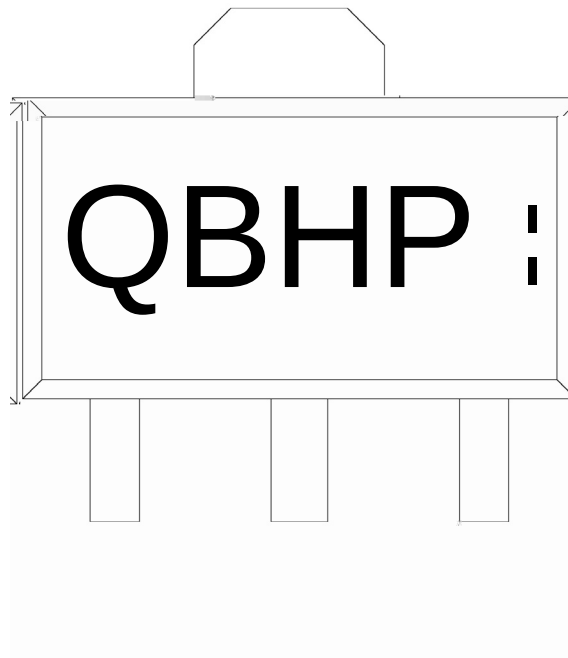
**mounted on $40 \times 40 \times 0.7mm$ ceramic board $40 \times 40 \times 0.7mm$ i

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=-50\mu A$ $I_E=0$	-80			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=-1.0mA$ $I_B=0$	-80			V

/ Electrical Characteristic Curve



/ Marking Instructions



Q: 汽车卤素-free 产品代码
BH: 产品类型
P: h_{FE} 分类符号
--: 批次代码, 批次代码变化与批次代码

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() / Temperature Profile for IR Reflow Soldering(Pb-Free)

℃

Note:

1. 150~200℃, Time: 60~120sec;

1.Preheating:150~200℃, Time:60~120sec.

2. 255±5℃, Time: 5~0.5sec;

2.Peak Temp.:255±5℃, Duration:5~0.5sec.

3. Cooling Speed: 2~10℃/sec.

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/ Resistance to Soldering Heat Test Conditions

260±5℃

10±1 sec.

Temp.:260±5

Time:10±1 sec